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Modified derivative superposition method for linearizing FET **low-noise amplifiers**

[Google Scholar](#) · [99.51.244.77:823](#) · [Aparin V](#) · [IEEE Transactions on Microwave Theory and Techniques](#)

Publication 2005

Intermodulation distortion in field-effect transistors (FETs) at RF frequencies is analyzed using the Volterra-series analysis. The degrading effect of the circuit reactances on the maximum IIP 3 in the conventional derivative-superposition (DS) method is explained. The ...

A **noise** optimization technique for integrated **low-noise amplifiers**

[Google Scholar](#) · [www.eng.auth.gr](#) · [Goo J](#) · [IEEE Journal of Solid-State Circuits](#)

Publication 2002

Based on measured four-**noise** parameters and two-port **noise** theory, considerations for **noise** optimization of integrated **low-noise** amplifier (LNA) designs are presented. If arbitrary values of source impedance are allowed, optimal **noise** performance of the LNA is obtained ...

Design of microwave GaAs MESFET's for broad-band **low-noise amplifiers**

[Google Scholar](#) · [pdfs.semanticscholar.org](#) · [Fukui H](#) · [IEEE Transactions on microwave theory and techniques](#)

Publication 1979

As a basis for designing GaAs MESFET's for broad-band **low-noise amplifiers**, the fundamental relationships between basic device parameters, and two-port **noise** parameters are investigated in a semiempirical manner. A set of four **noise** parameters are shown as ...

Dual-band high-linearity variable-gain **low-noise amplifiers** for wireless applications

[Google Scholar](#) · [ieeexplore.ieee.org](#) · [Fong K](#) · 1999 IEEE International Solid-State Circuits Conference. Digest of Technical Papers. ISSCC. First Edition (Cat. No. 99CH36278)

Publication 1999

A typical dual-band RF receiver front-end architecture is shown. The **low-noise amplifiers** (LNA) should have **low noise** figures to increase sensitivity of the receivers, and high linearity to prevent interference from undesired adjacent-channel signals. To increase the ...

The design of **low-noise amplifiers**

[Google Scholar](#) · [ieeexplore.ieee.org](#) · [Netzer Y](#) · [Proceedings of the IEEE](#)

Publication 1981

The essential theory and practical considerations for the design of **low-noise amplifiers** are gathered and organized to a uniform presentation. The relevant material is quite simple and straightforward, hopefully bringing within the reach of the interested circuit designer the "art" ...

Linearization techniques for CMOS **low noise amplifiers**: A tutorial

[Google Scholar](#) · [ieeexplore.ieee.org](#) · [Zhang H](#) · [IEEE Transactions on Circuits and Systems I: Regular Papers](#)

Publication 2010

This tutorial catalogues and analyzes previously reported CMOS **low noise** amplifier (LNA) linearization techniques. These techniques comprise eight categories: a) feedback; b) harmonic termination; c) optimum biasing; d) feedforward; e) derivative superposition (DS); f) ...

Using capacitive cross-coupling technique in RF **low noise amplifiers** and down-conversion mixer design

[Google Scholar](#) · [pure.tue.nl](#) · [Zhuo W](#) · [Proceedings of the 26th European Solid-State Circuits Conference](#)

Publication 2000

IPR2019-00128

Qualcomm 2023, p. 1

We report an approach to improve the **noise** performance of RF **low noise amplifiers** (LNAs) and down-conversion mixers. The technique we described here is based on capacitive cross-coupling across the two sides of a differential input stage. A LNA and mixer have been ...

Performance of dual-gate GaAs MESFET's as gain-controlled **low-noise amplifiers** and high-speed modulators

Google Scholar • [ieeexplore.ieee.org](#) • Liechti C • IEEE Transactions on Microwave Theory and Techniques
Publication 1975

This paper describes the microwave performance of GaAs FET's with two 1- μ m Schottky-barrier gates (dual-gate MESFET). At 10 GHz the MESFET, with an inductive second-gate termination, exhibits an 18-dB gain with -26-dB reverse isolation. Variation of the second ...

Concurrent multiband **low-noise amplifiers**-theory, design, and applications

Google Scholar • [authors.library.caltech.edu](#) • Hashemi H • IEEE Transactions on Microwave Theory and techniques
Publication 2002

The concept of concurrent multiband **low-noise-amplifiers** (LNAs) is introduced. A systematic way to design concurrent multiband integrated LNAs in general is developed. Applications of concurrent multiband LNAs in concurrent multiband receivers together with receiver ...

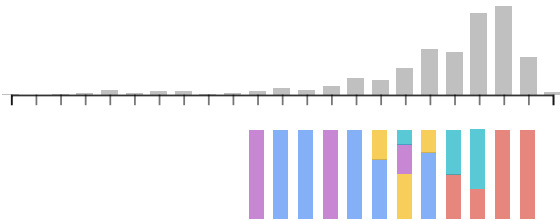
Cryogenic wide-band ultra-**low-noise** IF **amplifiers** operating at ultra-**low** DC power

Google Scholar • [www.physics.orst.edu](#) • Wadefalk N • IEEE Transactions on Microwave Theory and Techniques
Publication 2003

This paper describes cryogenic broad-band **amplifiers** with very **low** power consumption and very **low noise** for the 4-8-GHz frequency range. At room temperature, the two-stage InP-based amplifier has a gain of 27 dB and a **noise** temperature of 31 K with a power ...

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